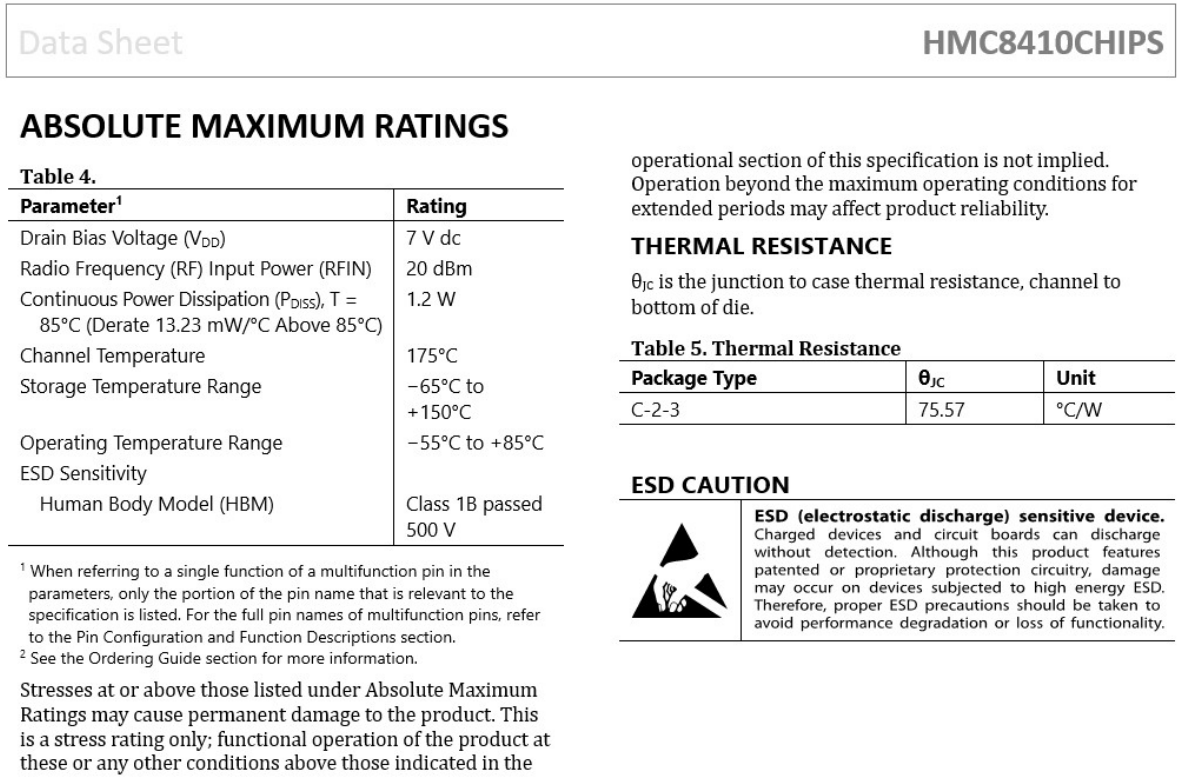
HMC8410 Die Rev C Datasheet changed Thermal Resistance from 75.57 to 125.85 °C/W. New 125.85 °C/W value is the result of an updated thermal analysis reflecting more accurately the device performance.

Rev B



Data Sheet HMC8410CHIPS

ABSOLUTE MAXIMUM RATINGS

Table 4.

Parameter[1]	Rating
Drain Bias Voltage (V_{DD})	7 V dc
Radio Frequency (RF) Input Power (RFIN)	20 dBm
Continuous Power Dissipation (P_{DISS}), T = 85°C (Derate 13.23 mW/°C Above 85°C)	1.2 W
Channel Temperature	175°C
Storage Temperature Range	−65°C to +150°C
Operating Temperature Range	−55°C to +85°C
ESD Sensitivity	
Human Body Model (HBM)	Class 1B passed 500 V

[1] When referring to a single function of a multifunction pin in the parameters, only the portion of the pin name that is relevant to the specification is listed. For the full pin names of multifunction pins, refer to the Pin Configuration and Function Descriptions section.

[2] See the Ordering Guide section for more information.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

THERMAL RESISTANCE

θ_{JC} is the junction to case thermal resistance, channel to bottom of die.

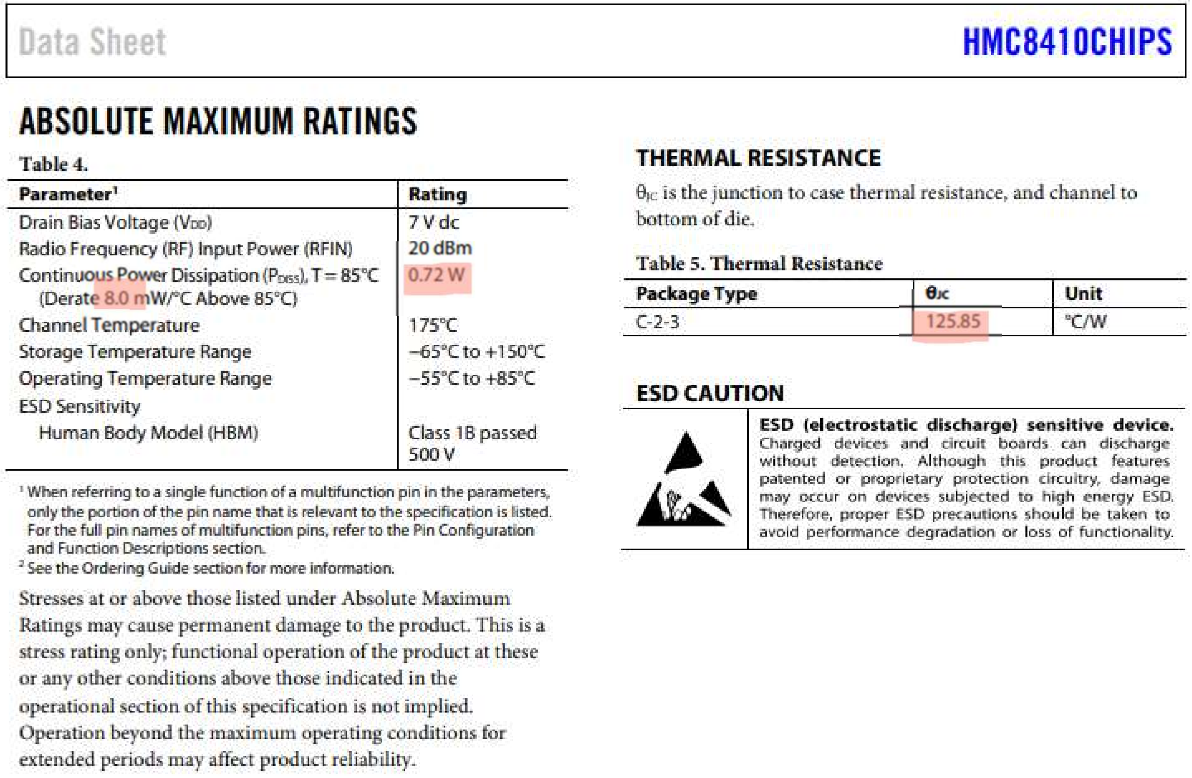
Table 5. Thermal Resistance

Package Type	θ_{JC}	Unit
C-2-3	75.57	°C/W

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

Rev C (3/2020)



Data Sheet HMC8410CHIPS

ABSOLUTE MAXIMUM RATINGS

Table 4.

Parameter[1]	Rating
Drain Bias Voltage (V_{DD})	7 V dc
Radio Frequency (RF) Input Power (RFIN)	20 dBm
Continuous Power Dissipation (P_{DISS}), T = 85°C (Derate 8.0 mW/°C Above 85°C)	0.72 W
Channel Temperature	175°C
Storage Temperature Range	−65°C to +150°C
Operating Temperature Range	−55°C to +85°C
ESD Sensitivity	
Human Body Model (HBM)	Class 1B passed 500 V

[1] When referring to a single function of a multifunction pin in the parameters, only the portion of the pin name that is relevant to the specification is listed. For the full pin names of multifunction pins, refer to the Pin Configuration and Function Descriptions section.

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THERMAL RESISTANCE

θ_{JC} is the junction to case thermal resistance, and channel to bottom of die.

Table 5. Thermal Resistance

Package Type	θ_{JC}	Unit
C-2-3	125.85	°C/W

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.